2SJ419-VB Datasheet

P-Channel 12-V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
- 12	0.0050 at V_{GS} = - 4.5 V	- 16
	0.0065 at V_{GS} = - 2.5 V	- 15
	0.0100 at V_{GS} = - 1.8 V	- 13

FEATURES

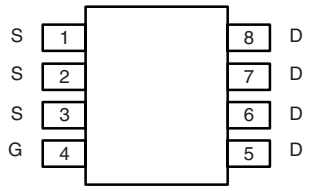
- **Halogen-free According to IEC 61249-2-21 Definition**
- Trench Power MOSFET
- Compliant to RoHS Directive 2002/95/EC

Pb-free
RoHS COMPLIANT
HALOGEN FREE Available

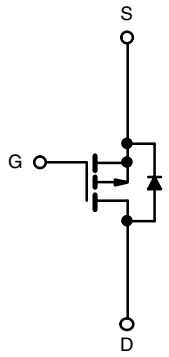
APPLICATIONS

- Load Switch
- Battery Switch

SO-8



Top View



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted					
Parameter		**Symbol**	**10 s**	**Steady State**	**Unit**
Drain-Source Voltage		V_{DS}	- 12		V
Gate-Source Voltage		V_{GS}	± 8		
Continuous Drain Current (T_J = 150 °C)[a]	T_A = 25 °C	I_D	- 16	- 10	A
	T_A = 70 °C		- 11.5	- 8	
Pulsed Drain Current		I_{DM}	- 50		
Continuous Source Current (Diode Conduction)[a]		I_S	- 2.7	- 1.36	
Maximum Power Dissipation[a]	T_A = 25 °C	P_D	3.0	1.5	W
	T_A = 70 °C		1.9	0.95	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		**Symbol**	**Typical**	**Maximum**	**Unit**
Maximum Junction-to-Ambient[a]	t ≤ 10 s	R_{thJA}	33	42	°C/W
	Steady State		70	84	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	16	21	

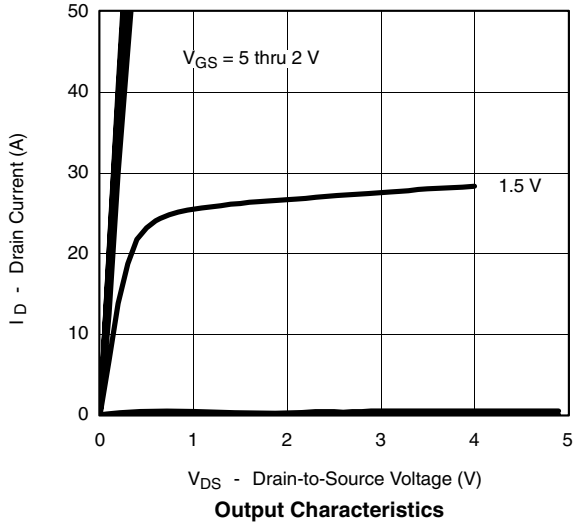
Notes:
a. Surface Mounted on 1" x 1" FR4 board.

SPECIFICATIONS T_J = 25 °C, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = - 600 µA	- 0.5	-	1.0	V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 8 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = - 12 V, V_{GS} = 0 V			- 1	µA
		V_{DS} = - 12 V, V_{GS} = 0 V, T_J = 70 °C			- 10	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} = - 5 V, V_{GS} = - 4.5 V	- 30			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = - 4.5 V, I_D = - 14 A		0.0050		Ω
		V_{GS} = - 2.5 V, I_D = - 13 A		0.0065		
		V_{GS} = - 1.8 V, I_D = - 12 A		0.0100		
Forward Transconductance[a]	g_{fs}	V_{DS} = - 6 V, I_D = - 14 A		80		S
Diode Forward Voltage[a]	V_{SD}	I_S = - 2.7 A, V_{GS} = 0 V		- 0.6	- 1.1	V
Dynamic[b]						
Total Gate Charge	Q_g	V_{DS} = - 6 V, V_{GS} = - 5 V, I_D = - 14 A		110	165	nC
Gate-Source Charge	Q_{gs}			15		
Gate-Drain Charge	Q_{gd}			27.5		
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = - 6 V, R_L = 6 Ω I_D ≅ - 1 A, V_{GEN} = - 4.5 V, R_g = 6 Ω		110	170	ns
Rise Time	t_r			235	350	
Turn-Off Delay Time	$t_{d(off)}$			410	620	
Fall Time	t_f			285	430	
Gate Resistance	R_g			3.6		Ω
Source-Drain Reverse Recovery Time	t_{rr}	I_F = - 2.1 A, dI/dt = 100 A/µs		180	270	ns

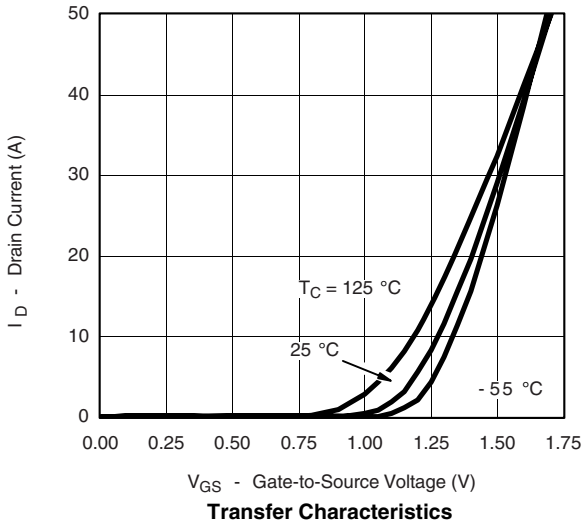
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C unless otherwise noted

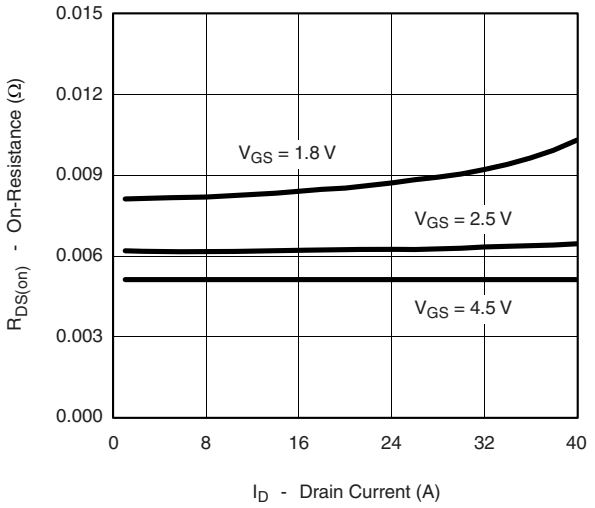


Output Characteristics

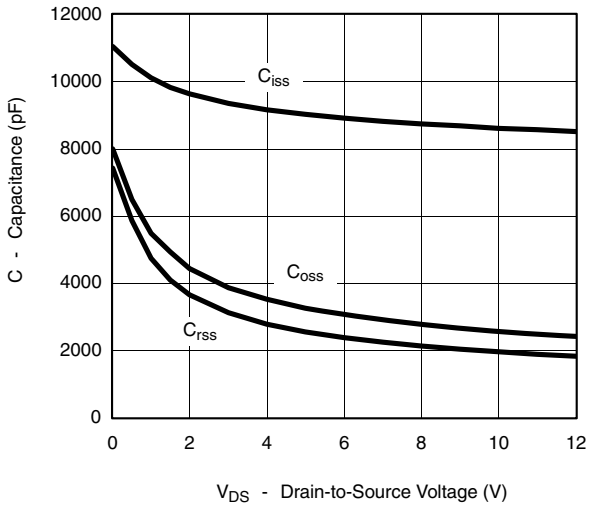


Transfer Characteristics

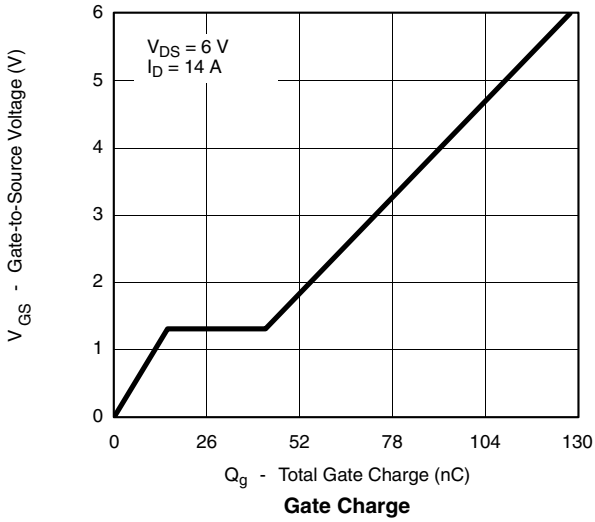
TYPICAL CHARACTERISTICS 25 °C unless otherwise noted



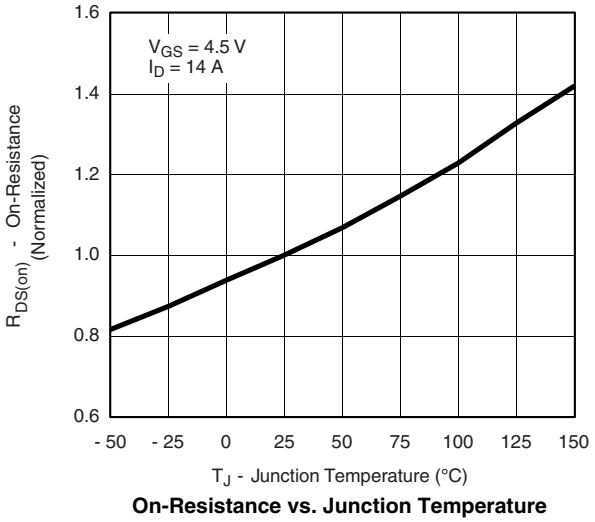
On-Resistance vs. Drain Current



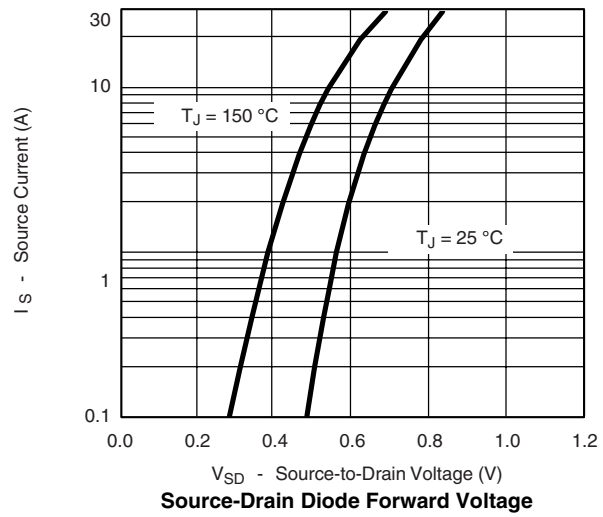
Capacitance



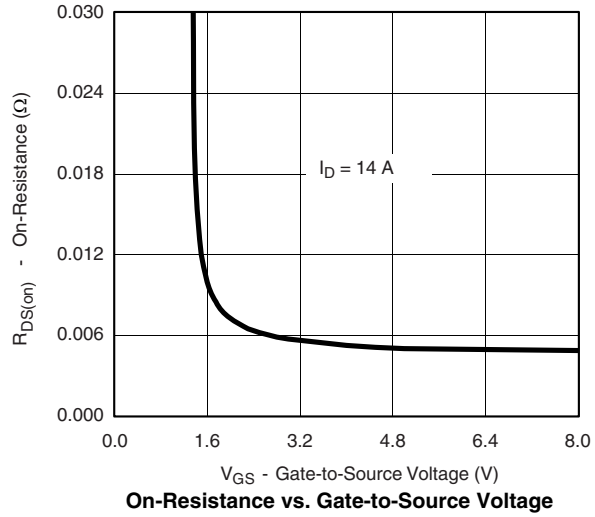
Gate Charge



On-Resistance vs. Junction Temperature

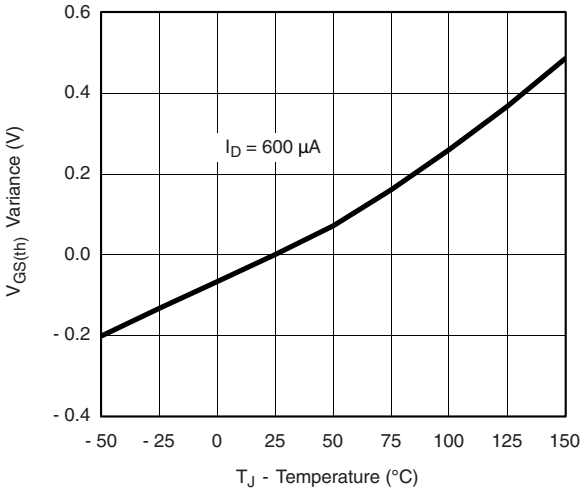


Source-Drain Diode Forward Voltage

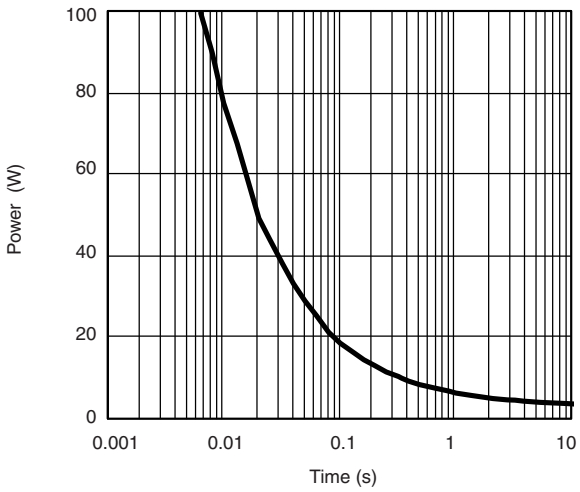


On-Resistance vs. Gate-to-Source Voltage

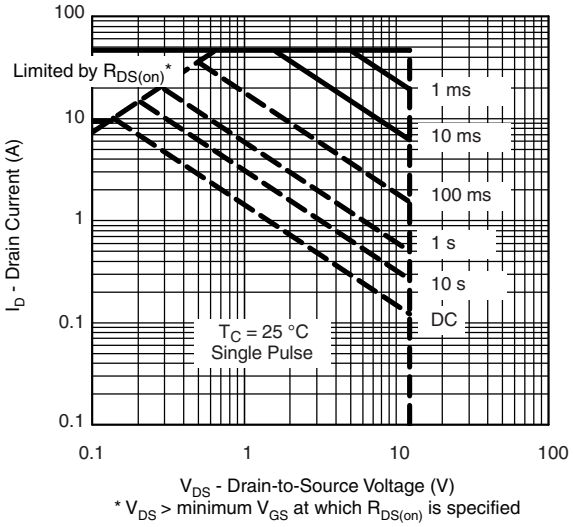
TYPICAL CHARACTERISTICS 25 °C unless otherwise noted



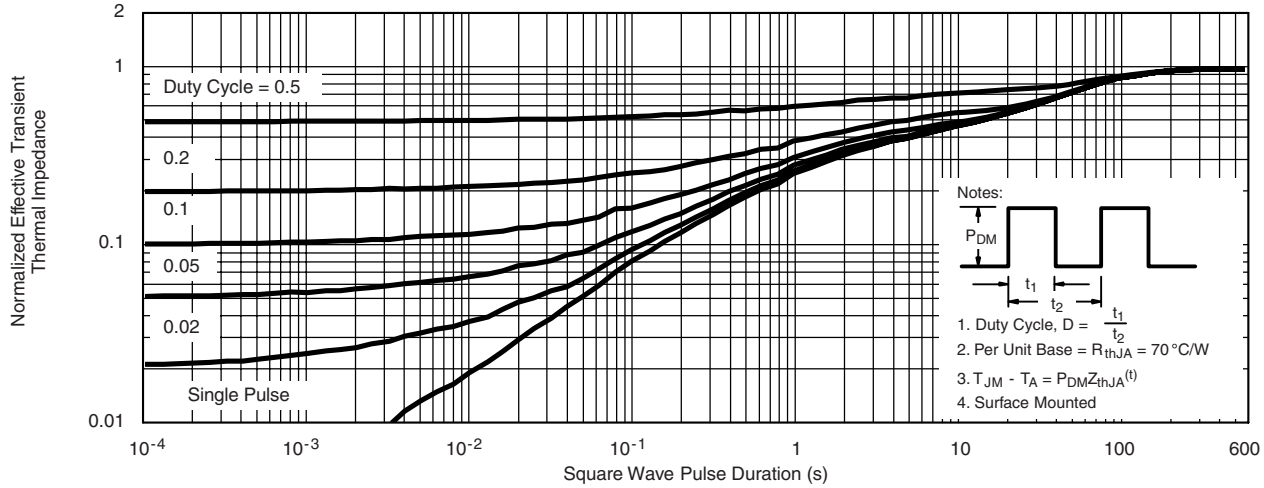
Threshold Voltage



Single Pulse Power, Junction-to-Ambient

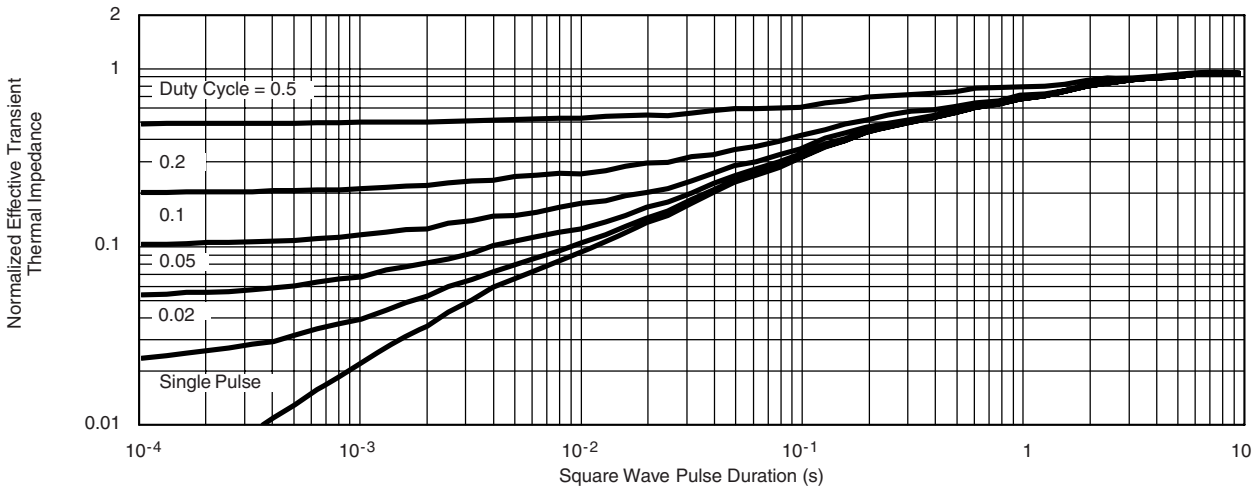


Safe Operating Area, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient

TYPICAL CHARACTERISTICS 25 °C unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

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